

ABSTRACT OF Korean Patent Application No. 10-2000-0036823

There is provided a semiconductor memory device and a method for fabricating the same. According to the present invention, the semiconductor memory device is efficiently capable of efficiently preventing plug's oxidation caused by forming a dielectric layer in an oxidation ambient of high temperature. In order to overcome plug's oxidation in a process of forming a dielectric layer requiring an oxygen ambient of high temperature such as BST, PZT and SBT, a plug is formed of platinum having excellent electric conductivity and high-temperature acrotolerant characteristic. In addition, a capacitor bottom electrode for storage is formed by stacking IrO₂ and Pt, which have excellent oxygen-diffusion prevention characteristic.